

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L4	21964	(box (buried near oxide) soi sos (silicon adj on adj insulator)) same epitax\$8	US-PGPUB; USPAT	OR	ON	2005/09/03 16:27
L5	69	L4 same ((silicon si semiconductor) near2 (oxygen near (rich dop\$6 implant\$6)))	US-PGPUB; USPAT	OR	ON	2005/09/03 15:32
L6	432	(silicon si semiconductor) near2 (oxygen near (rich dop\$6))	US-PGPUB; USPAT	OR	ON	2005/09/03 16:26
L7	112	(silicon si semiconductor) near2 (oxygen near rich)	US-PGPUB; USPAT	OR	ON	2005/09/03 15:55
L8	4046	438/300.ccls. 438/305.ccls. 438/306.ccls. 438/307.ccls. 438/502.ccls. 438/509.ccls. 438/765.ccls. 438/769.ccls. 438/770.ccls. 438/773.ccls. 438/775.ccls.	US-PGPUB; USPAT	OR	OFF	2005/09/03 15:33
L9	37	L8 and ((silicon si semiconductor) near2 (oxygen near (rich dop\$6 implant\$6)))	US-PGPUB; USPAT	OR	ON	2005/09/03 15:33
L10	96	(box (buried near oxide) soi sos (silicon adj on adj insulator)) and ((silicon si semiconductor) near2 (oxygen near (rich dop\$6 implant\$6)))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/03 16:22
L11	17	(silicon si semiconductor) near2 (oxygen near rich)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/03 16:21
L13	14	("5223919" "5461243" "5714777" "5759898" "6077343").PN. OR ("6369438").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/09/03 16:18
L14	3	jp-56121780-.did. jp-62210673-.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/03 16:19
L15	128	(silicon si semiconductor) near2 (oxygen near dop\$6)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/03 16:21
L16	16	15 and (box (buried near oxide) soi sos (silicon adj on adj insulator))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/03 16:22
L17	322	(silicon si semiconductor) near2 (oxygen near dop\$6)	US-PGPUB; USPAT	OR	ON	2005/09/03 16:27
L18	74	17 same ((box (buried near oxide) soi sos (silicon adj on adj insulator)) epitax\$8)	US-PGPUB; USPAT	OR	ON	2005/09/03 17:09

L19	335	(gate near (insulat\$6 dielectric oxide dioxide) same ((native adj oxide) with (etch\$6 remov\$6))	US-PGPUB; USPAT	OR	ON	2005/09/03 17:11
L20	35	19 same quality	US-PGPUB; USPAT	OR	ON	2005/09/03 17:11
S1	3	"20020135020".pn. "20020097608".pn. "6369438".pn.	US-PGPUB; USPAT	OR	OFF	2005/09/02 16:38
S2	4046	438/300.ccls. 438/305.ccls. 438/306.ccls. 438/307.ccls. 438/502.ccls. 438/509.ccls. 438/765.ccls. 438/769.ccls. 438/770.ccls. 438/773.ccls. 438/775.ccls.	US-PGPUB; USPAT	OR	OFF	2005/09/02 17:51
S3	185	438/773.ccls.	US-PGPUB; USPAT	OR	OFF	2005/09/02 16:41
S4	21964	(box (buried near oxide) soi sos (silicon adj on adj insulator)) same epitax\$8	US-PGPUB; USPAT	OR	ON	2005/09/02 18:00
S5	437	S2 and S4	US-PGPUB; USPAT	OR	ON	2005/09/02 18:03
S7	603	(box (buried near oxide) soi sos (silicon adj on adj insulator)) same ((silicon si semiconductor) near2 (oxygen near (rich dop\$6 implant\$6)))	US-PGPUB; USPAT	OR	ON	2005/09/02 18:01